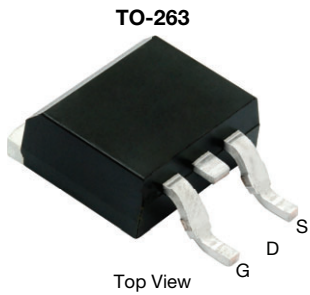


## Automotive N-Channel 30 V (D-S) 175 °C MOSFET



### FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	30
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.00135
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V	0.00175
I <sub>D</sub> (A)	120
Configuration	Single
Package	TO-263

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	30	V
Gate-source voltage		V <sub>GS</sub>	± 20	
Continuous drain current <sup>a</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	120	A
	T <sub>C</sub> = 125 °C		120	
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	120	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	360	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	72	
Single pulse avalanche energy		E <sub>AS</sub>	259	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	375	W
	T <sub>C</sub> = 125 °C		125	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	0.4	

### Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)



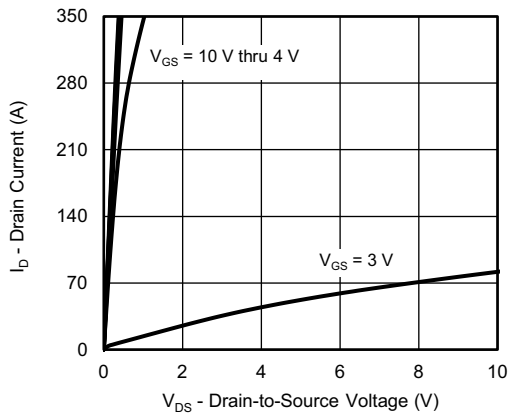
SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	30	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1.5	2.0	2.5	
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 30\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 30\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 30\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	800	$\mu\text{A}$
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} \geq 5\text{ V}$	100	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$	-	0.00110	0.00135	$\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	0.00191	
		$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	0.00220	
		$V_{GS} = 4.5\text{ V}$ , $I_D = 35\text{ A}$	-	0.00143	0.00175	$\Omega$
Forward transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 40\text{ A}$	-	233	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 15\text{ V}$ , $f = 1\text{ MHz}$	-	20 090	28 000	$\mu\text{F}$
Output capacitance	$C_{oss}$		-	7000	9500	
Reverse transfer capacitance	$C_{rss}$		-	540	750	
Total gate charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 15\text{ V}$ , $I_D = 50\text{ A}$	-	295	450	nC
Gate-source charge <sup>c</sup>	$Q_{gs}$		-	59	-	
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	59	-	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.5	1.11	1.7	$\Omega$
Turn-on delay time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 15\text{ V}$ , $R_L = 0.2\text{ }\Omega$ $I_D \cong 50\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$	-	30	45	ns
Rise time <sup>c</sup>	$t_r$		-	240	360	
Turn-off delay time <sup>c</sup>	$t_{d(off)}$		-	98	150	
Fall time <sup>c</sup>	$t_f$		-	44	70	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>						
Pulsed current <sup>a</sup>	$I_{SM}$		-	-	360	A
Forward voltage	$V_{SD}$	$I_F = 60\text{ A}$ , $V_{GS} = 0\text{ V}$	-	0.8	1.5	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 35\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	96	195	ns
Body diode reverse recovery charge	$Q_{rr}$		-	185	370	nC
Reverse recovery fall time	$t_a$		-	48	-	ns
Reverse recovery rise time	$t_b$		-	48	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$			-	-3.4	-

**Notes**

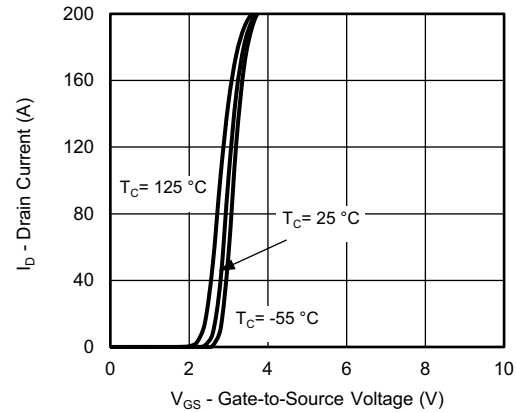
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing  
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

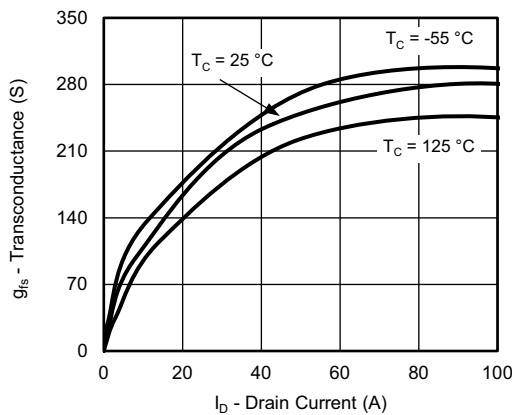
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



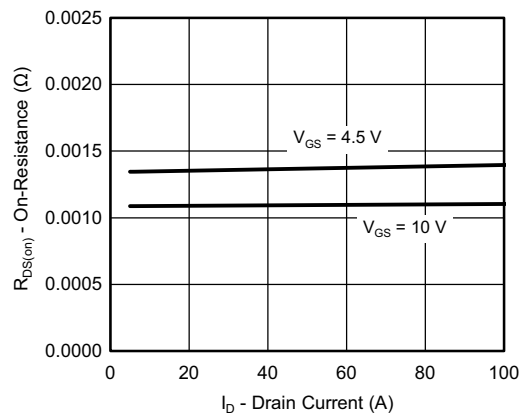
**Output Characteristics**



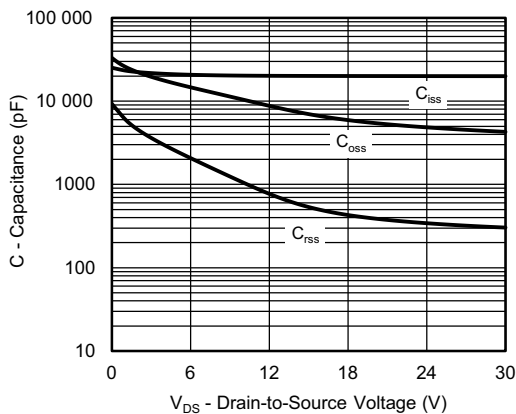
**Transfer Characteristics**



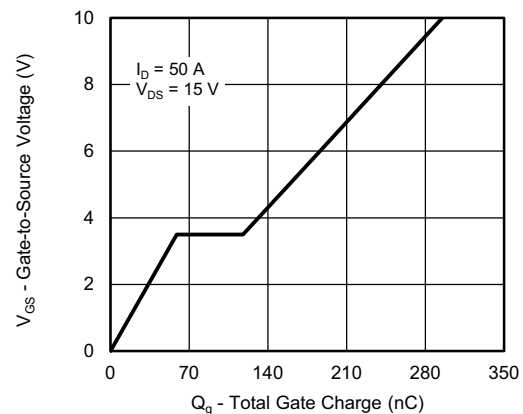
**Transconductance**



**On-Resistance vs. Drain Current**



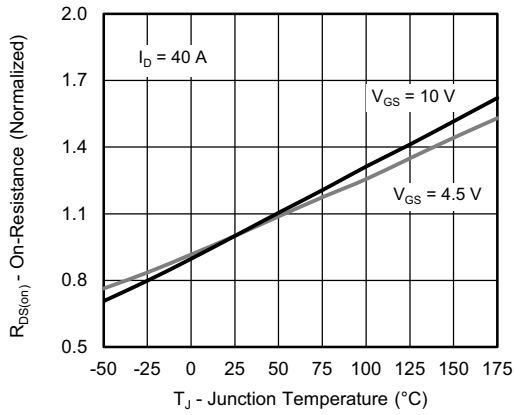
**Capacitance**



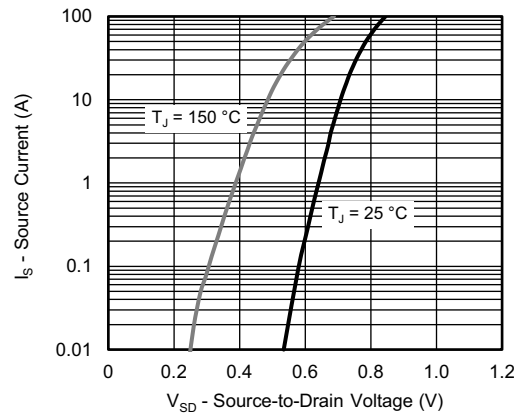
**Gate Charge**



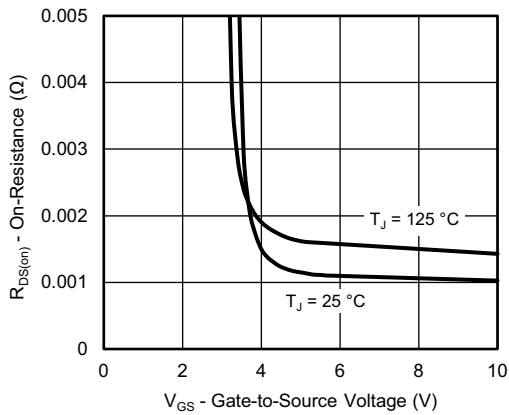
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



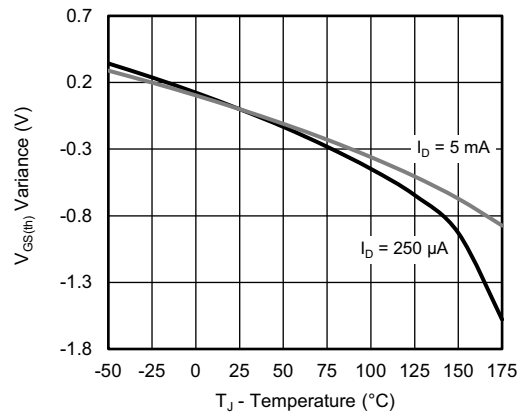
**On-Resistance vs. Junction Temperature**



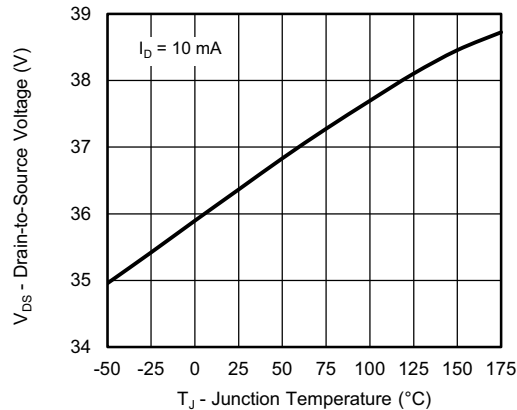
**Source Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



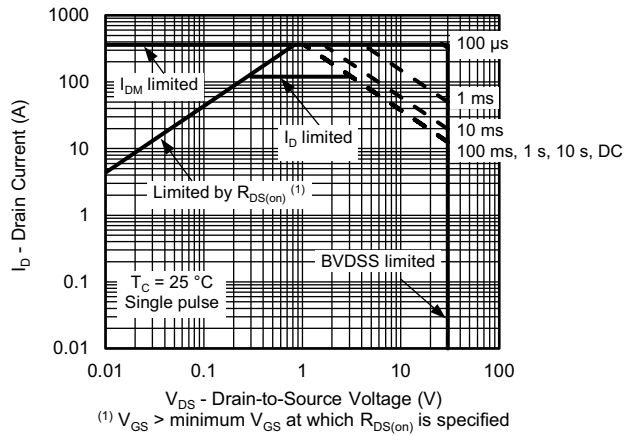
**Threshold Voltage**



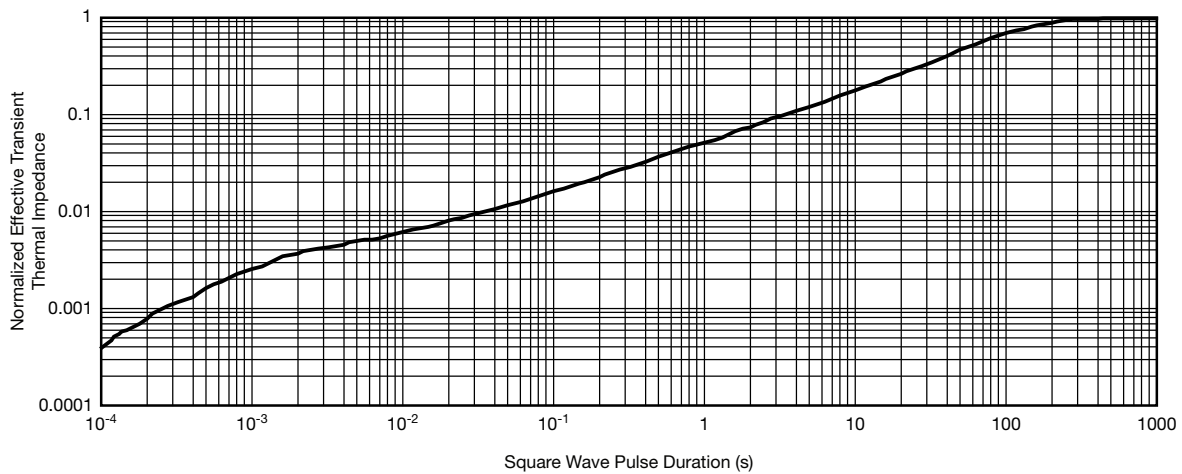
**Drain Source Breakdown vs. Junction Temperature**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



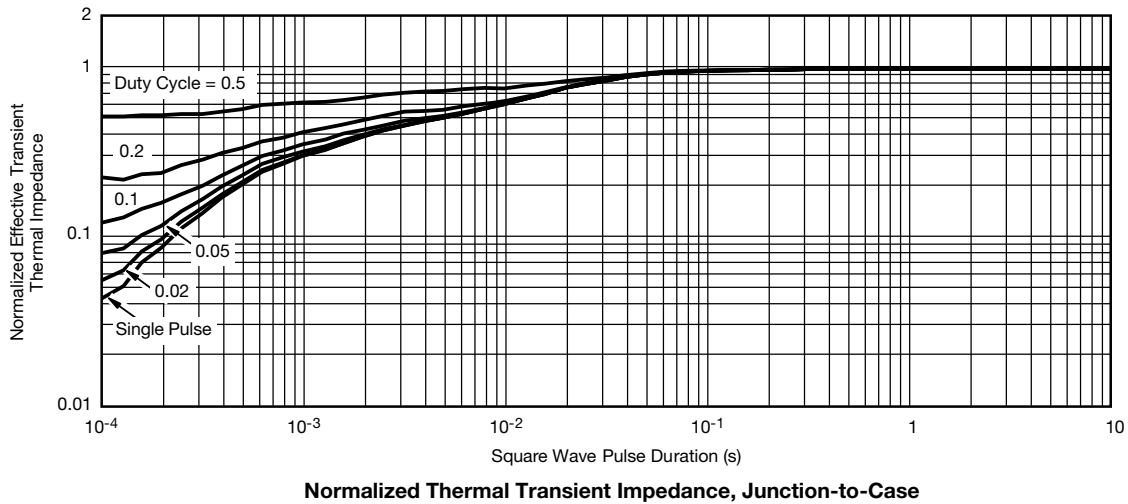
**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



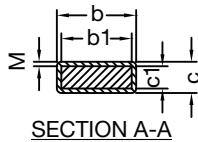
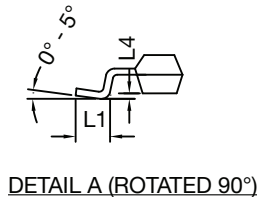
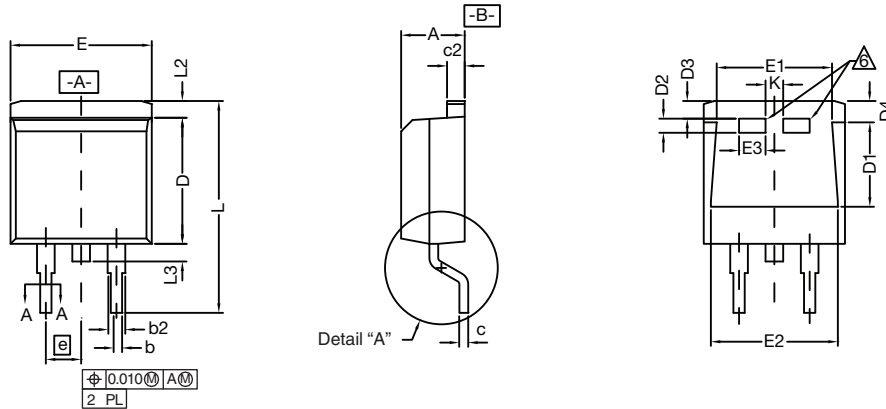
**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

**VERSION 1: FACILITY CODE = T**



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
<b>E2</b>	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	

**Notes**

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.



**VERSION 2: FACILITY CODE = N**



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
c	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.54 BSC	
H	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78	5.28
J1	2.56	2.96
ECN: S24-1080-Rev. L, 28-Oct-2024		
DWG: 5843		



**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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